

ABSTRACT

A semiconductor device comprises an embedded insulation layer 101 formed on a semiconductor substrate 100, plural power semiconductor elements 2, 3 formed on a semiconductor substrate 100 on the embedded insulation layer, a trench 4 formed on the semiconductor substrate and isolating between the power semiconductor elements, and an isolator 5 insulating and driving control electrodes of the power semiconductor elements, and the power semiconductor elements 2, 3 such as transistors can be used, being connected each other in series.

[SELECTED FIGURE] Fig. 2